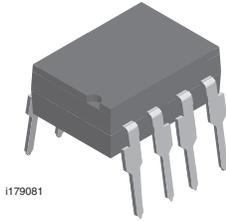
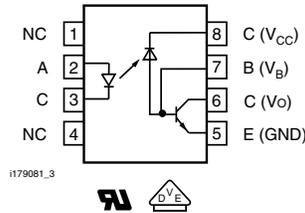


High Speed Optocoupler, 1 MBd, Photodiode with Transistor Output, 110 °C Rated



1179081



1179081_3



FEATURES

- Operating temperature from - 55 °C to + 110 °C
- Isolation test voltages: 5300 V_{RMS}
- TTL compatible
- High bit rates: 1 MBd
- Bandwidth 2 MHz
- Open-collector output
- External base wiring possible
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC


RoHS
COMPLIANT

DESCRIPTION

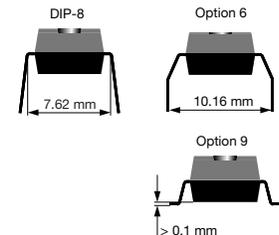
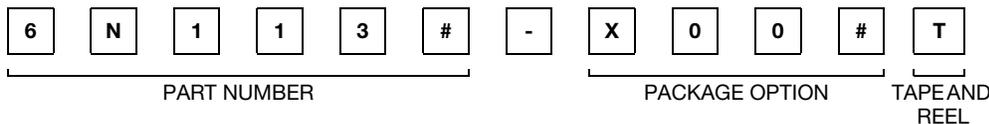
The 6N1135 and 6N1136 are 110 °C rated optocouplers with a GaAlAs infrared emitting diode, optically coupled with an integrated photo detector which consists of a photo diode and a high-speed transistor in a DIP-8 plastic package.

Signals can be transmitted between two electrically separated circuits up to frequencies of 2 MHz. The potential difference between the circuits to be coupled should not exceed the maximum permissible reference voltages.

AGENCY APPROVALS

- UL1577, file no. E52744 system code H or J
- DIN EN 60747-5-5 (VDE 0884)
- cUL - file no. E52744, equivalent to CSA bulletin 5A

ORDERING INFORMATION



AGENCY CERTIFIED/PACKAGE	CTR (%)	
UL	≥ 7	≥ 19
DIP-8	6N1135	6N1136
DIP-8, 400 mil, option 6	6N1135-X006	6N1136-X006
SMD-8, option 9	6N1135-X009T	6N1136-X009T

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C, unless otherwise specified)

PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V _R	5	V
Forward current		I _F	25	mA
Peak forward current	t = 1 ms, duty cycle 50 %	I _{FM}	50	mA
Maximum surge forward current	t ≤ 1 μs, 300 pulses/s	I _{FSM}	1	A
Thermal resistance		R _{th}	700	K/W
Power dissipation	T _{amb} = 70 °C	P _{diss}	45	mW
OUTPUT				
Supply voltage		V _{CC}	- 0.5 to 15	V
Output voltage		V _O	- 0.5 to 15	V
Emitter base voltage		V _{EBO}	5	V
Output current		I _O	8	mA
Maximum Output current			16	mA

Vishay Semiconductors High Speed Optocoupler, 1 MBd,
Photodiode with Transistor Output,
110 °C Rated

ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
OUTPUT				
Base current		I_B	5	mA
Thermal resistance			300	K/W
Power dissipation	$T_{amb} = 70\text{ }^{\circ}\text{C}$	P_{diss}	100	mW
COUPLER				
Isolation test voltage (between emitter and detector climate per DIN 50014 part 2, Nov. 74)	$t = 1\text{ s}$	V_{ISO}	5300	V_{RMS}
Storage temperature range		T_{stg}	- 55 to + 125	$^{\circ}\text{C}$
Ambient temperature range		T_{amb}	- 55 to + 100	$^{\circ}\text{C}$
Soldering temperature ⁽¹⁾	max. $\leq 10\text{ s}$, dip soldering $\geq 0.5\text{ mm}$ from case bottom	T_{sld}	260	$^{\circ}\text{C}$

Notes

- Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

⁽¹⁾ Refer to reflow profile for soldering conditions for surface mounted devices (SMD). Refer to wave profile for soldering conditions for through hole devices (DIP).

ELECTRICAL CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT							
Forward voltage	$I_F = 1.6\text{ mA}$		V_F		1.6	1.9	V
Breakdown voltage	$I_R = 10\text{ }\mu\text{A}$		V_{BR}	5			V
Reverse current	$V_R = 5\text{ V}$		I_R		0.5	10	μA
Capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$		C_I		125		pF
Temperature coefficient, forward voltage	$I_F = 1.6\text{ mA}$		$\Delta V_F/\Delta T_A$		- 1.7		mV/ $^{\circ}\text{C}$
OUTPUT							
Logic low supply current	$I_F = 1.6\text{ mA}$, $V_O = \text{open}$, $V_{CC} = 15\text{ V}$		I_{CCL}		150		μA
Logic high supply current	$I_F = 0\text{ mA}$, $V_O = \text{open}$, $V_{CC} = 15\text{ V}$		I_{CCH}		0.01	1	μA
Output voltage, output low	$I_F = 16\text{ mA}$, $V_{CC} = 4.5\text{ V}$, $I_O = 1.1\text{ mA}$,	6N1135	V_{OL}		0.1	0.4	V
	$I_F = 16\text{ mA}$, $V_{CC} = 4.5\text{ V}$, $I_O = 2.4\text{ mA}$	6N1136	V_{OL}		0.1	0.4	V
Output current, output high	$I_F = 0\text{ mA}$, $V_O = V_{CC} = 5.5\text{ V}$		I_{OH}		3	500	nA
	$I_F = 0\text{ mA}$, $V_O = V_{CC} = 15\text{ V}$		I_{OH}		0.01	1	μA
COUPLER							
Capacitance (input to output)	$f = 1\text{ MHz}$		C_{IO}		0.6		pF

Note

- Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

CURRENT TRANSFER RATIO							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
Current transfer ratio	$I_F = 16\text{ mA}$, $V_O = 0.4\text{ V}$, $V_{CC} = 4.5\text{ V}$	6N1135	CTR	7	16		%
		6N1136	CTR	19	35		%
	$I_F = 16\text{ mA}$, $V_O = 0.5\text{ V}$, $V_{CC} = 4.5\text{ V}$	6N1135	CTR	5			%
		6N1136	CTR	15			%

SWITCHING CHARACTERISTICS							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
High to low	$I_F = 16 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 4.1 \text{ k}\Omega$	6N1135	t_{PHL}		0.3	1.5	μs
	$I_F = 16 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1.9 \text{ k}\Omega$	6N1136	t_{PHL}		0.2	0.8	μs
Low to high	$I_F = 16 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 4.1 \text{ k}\Omega$	6N1135	t_{PLH}		0.3	1.5	μs
	$I_F = 16 \text{ mA}, V_{CC} = 5 \text{ V}, R_L = 1.9 \text{ k}\Omega$	6N1136	t_{PLH}		0.2	0.8	μs

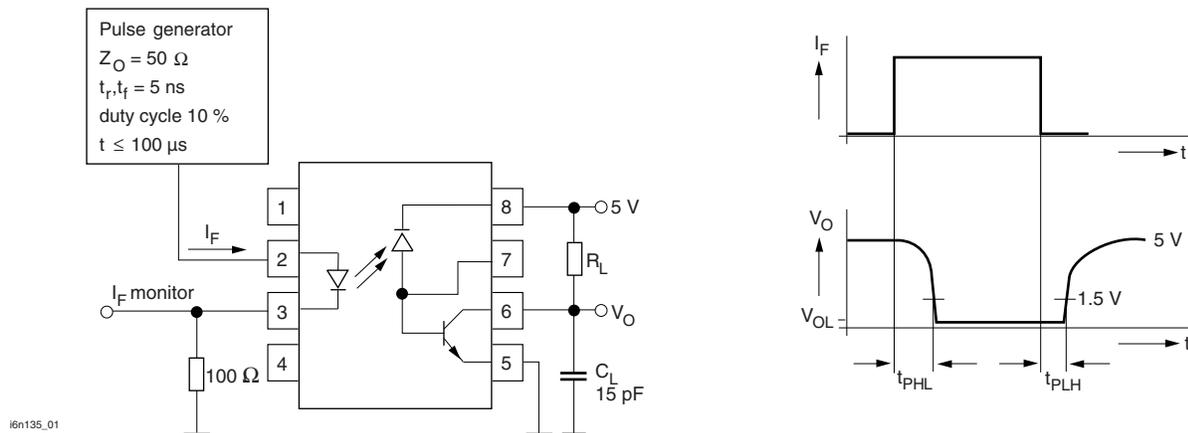


Fig. 1 - Switching Times

COMMON MODE TRANSIENT IMMUNITY							
PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
High	$I_F = 0 \text{ mA}, V_{CM} = 10 \text{ V}_{P-P}, V_{CC} = 5 \text{ V}, R_L = 4.1 \text{ k}\Omega$	6N1135	$ CM_H $		1000		$\text{V}/\mu\text{s}$
	$I_F = 0 \text{ mA}, V_{CM} = 10 \text{ V}_{P-P}, V_{CC} = 5 \text{ V}, R_L = 1.9 \text{ k}\Omega$	6N1136	$ CM_H $		1000		$\text{V}/\mu\text{s}$
Low	$I_F = 16 \text{ mA}, V_{CM} = 10 \text{ V}_{P-P}, V_{CC} = 5 \text{ V}, R_L = 4.1 \text{ k}\Omega$	6N1135	$ CM_L $		1000		$\text{V}/\mu\text{s}$
	$I_F = 16 \text{ mA}, V_{CM} = 10 \text{ V}_{P-P}, V_{CC} = 5 \text{ V}, R_L = 1.9 \text{ k}\Omega$	6N1136	$ CM_L $		1000		$\text{V}/\mu\text{s}$

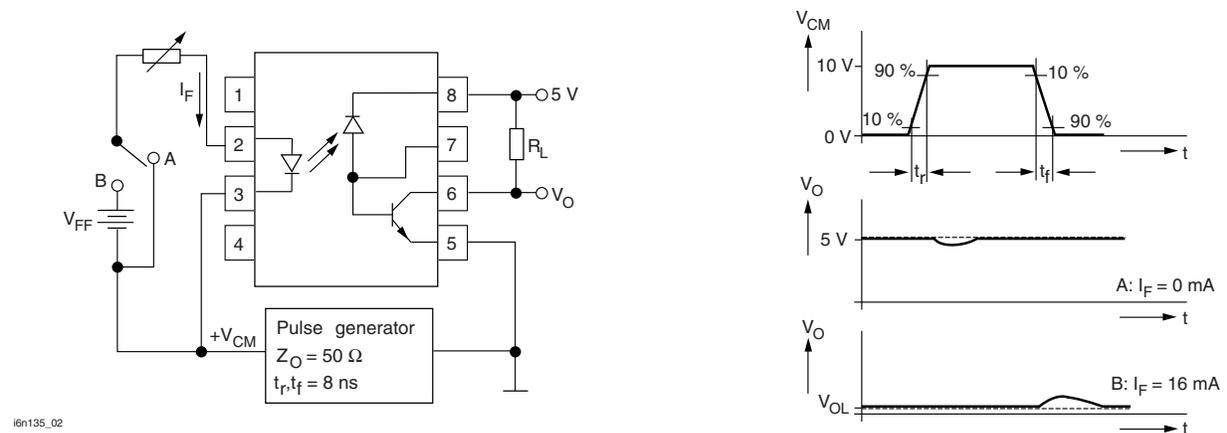


Fig. 2 - Common-Mode Interference Immunity

SAFETY AND INSULATION RATINGS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Climatic classification (according to IEC 68 part 1)				55/110/21		
Pollution degree (DIN VDE 0109)				2		
Comparative tracking index per DIN IEC112/VDE 0303 part 1, group IIIa per DIN VDE 6110		CTI	175		399	
V_{IOTM}		V_{IOTM}	8000			V
V_{IORM}		V_{IORM}	630			V
Isolation resistance	$V_{IO} = 500\text{ V}, T_{amb} = 25\text{ °C}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ °C}$	R_{IO}	10^{11}			Ω
P_{SI}		P_{SI}			500	mA
I_{SI}		I_{SI}			300	mW
T_{SI}		T_{SI}			175	°C
Creepage distance			7			mm
Clearance distance			7			mm
Insulation thickness			0.2			mm

Note

- As per IEC 60747-5-5, §7.4.3.8.1, this optocoupler is suitable for “safe electrical insulation” only within the safety ratings. Compliance with the safety ratings shall be ensured by means of protective circuits.

TYPICAL CHARACTERISTICS ($T_{amb} = 25\text{ °C}$, unless otherwise specified)

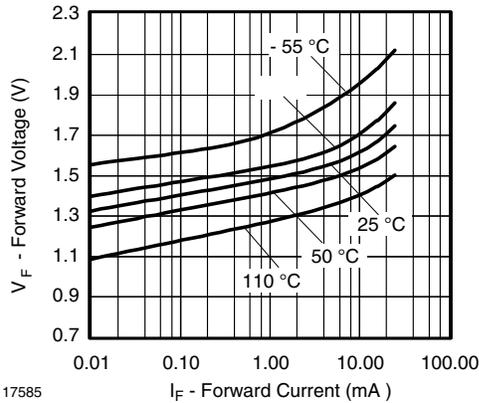


Fig. 3 - Forward Voltage vs. Forward Current

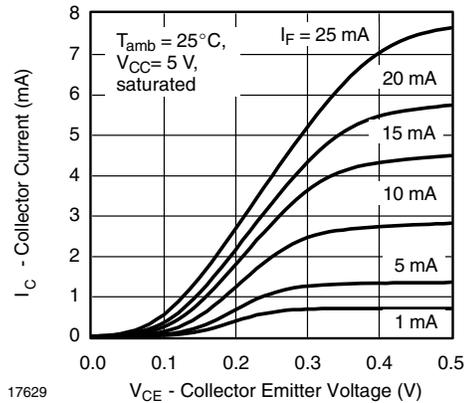


Fig. 5 - Collector Current vs. Collector Emitter Voltage

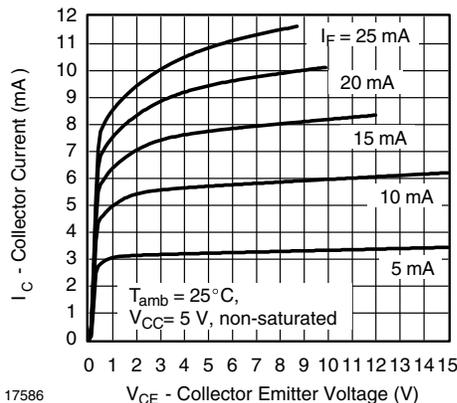


Fig. 4 - Collector Current vs. Collector Emitter Voltage

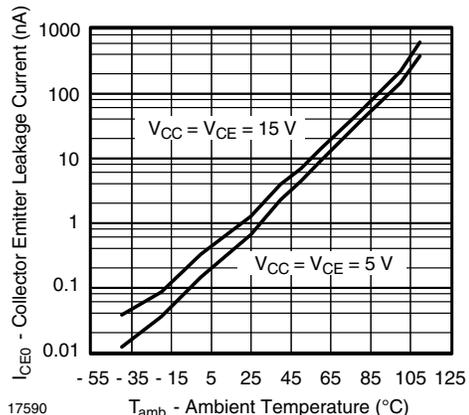


Fig. 6 - Collector Emitter Dark Current vs. Ambient Temperature

High Speed Optocoupler, 1 MBd, Vishay Semiconductors Photodiode with Transistor Output, 110 °C Rated

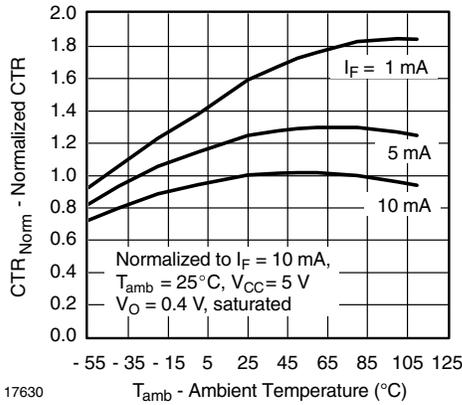


Fig. 7 - Normalized Current Transfer Ratio vs. Ambient Temperature

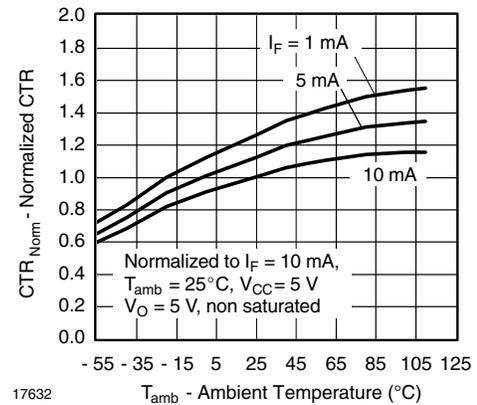


Fig. 10 - Normalized Current Transfer Ratio vs. Ambient Temperature

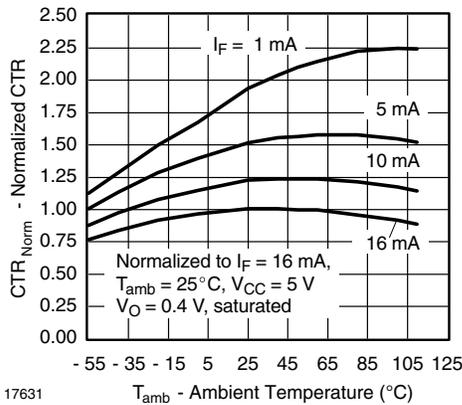


Fig. 8 - Normalized Current Transfer Ratio vs. Ambient Temperature

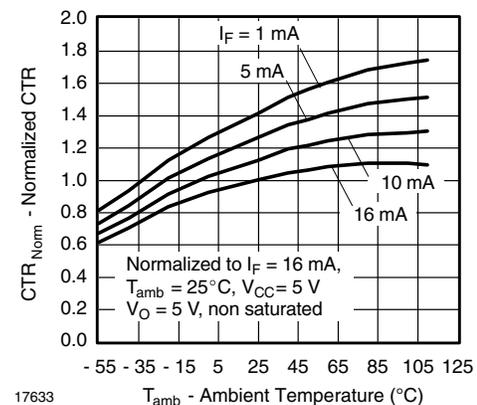


Fig. 11 - Normalized Current Transfer Ratio vs. Ambient Temperature

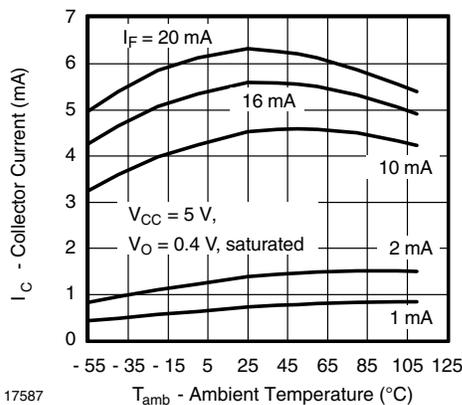


Fig. 9 - Output Current vs. Temperature

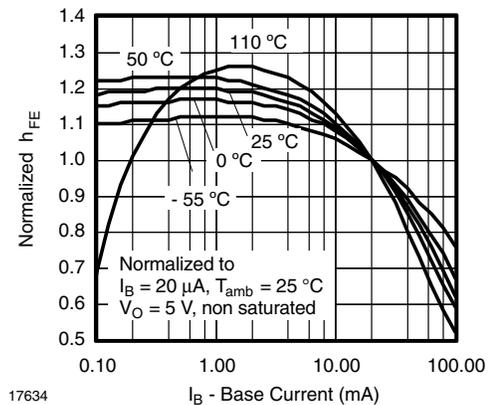
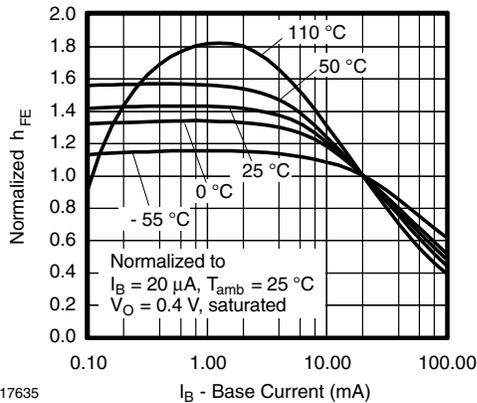


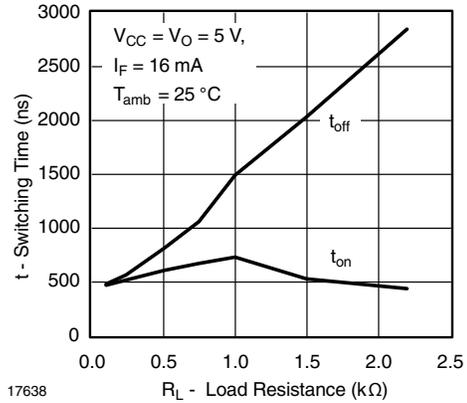
Fig. 12 - Normalized h_{FE} vs. Base Current

Vishay Semiconductors High Speed Optocoupler, 1 MBd,
Photodiode with Transistor Output,
110 °C Rated



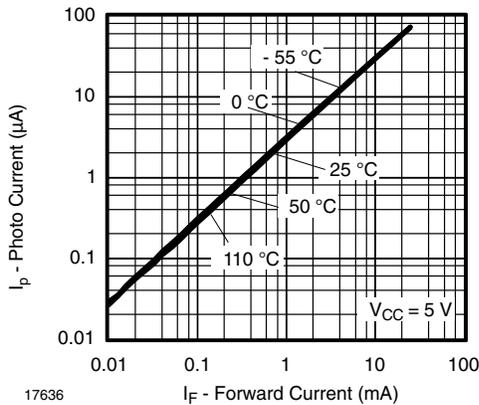
17635

Fig. 13 - Normalized h_{FE} vs. Base Current



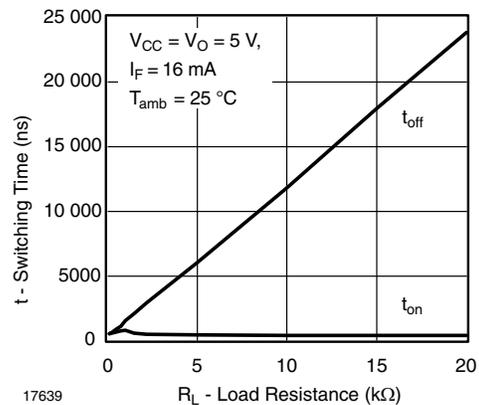
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Fig. 16 - Switching Time vs. Load Resistance



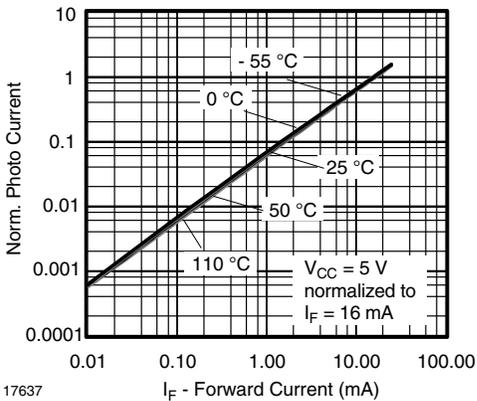
17636

Fig. 14 - Photo Current vs. Forward Current



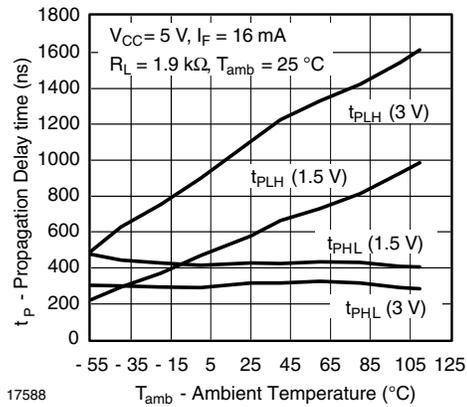
17639

Fig. 17 - Switching Time vs. Load Resistance



17637

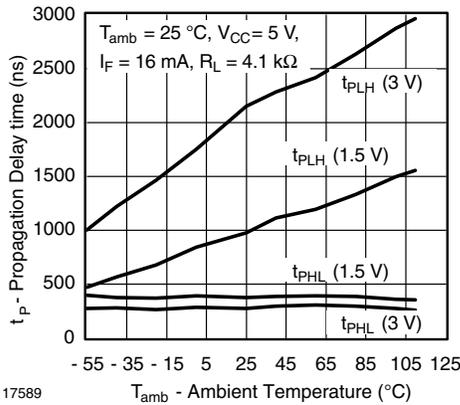
Fig. 15 - Photo Current vs. Forward Current



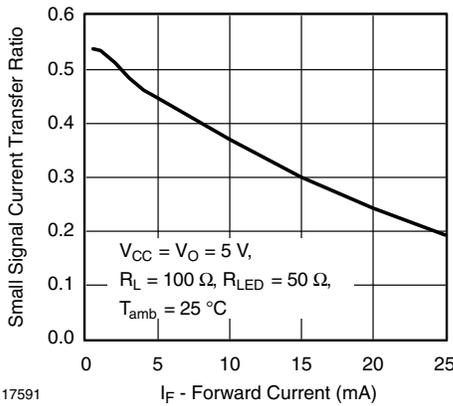
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Fig. 18 - Propagation Delay vs. Ambient Temperature

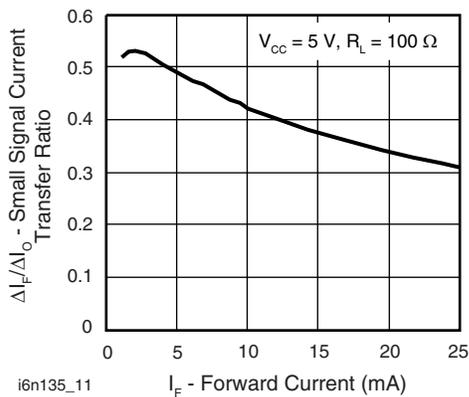
High Speed Optocoupler, 1 MBd, Vishay Semiconductors
 Photodiode with Transistor Output,
 110 °C Rated



17589 Fig. 19 - Propagation Delay vs. Ambient Temperature



17591 Fig. 20 - Small Signal CTR vs. Forward Current



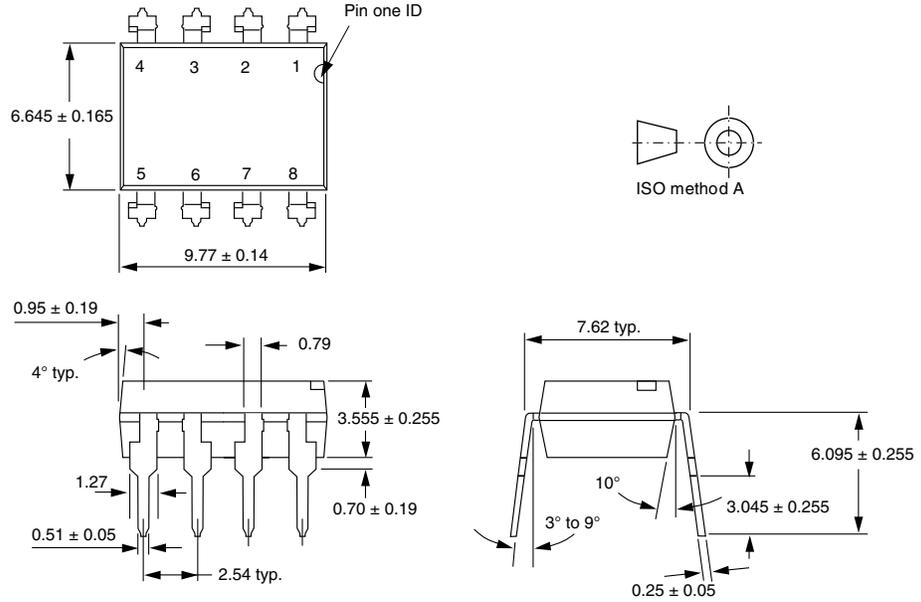
i6n135_11 Fig. 21 - Small Signal Current Transfer Ratio vs. Quiescent Input Current

6N1135, 6N1136



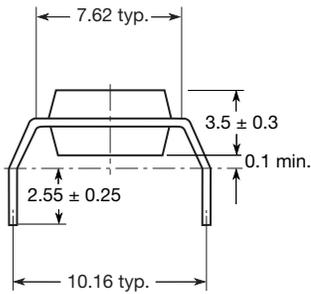
Vishay Semiconductors High Speed Optocoupler, 1 MBd,
Photodiode with Transistor Output,
110 °C Rated

PACKAGE DIMENSIONS in millimeters



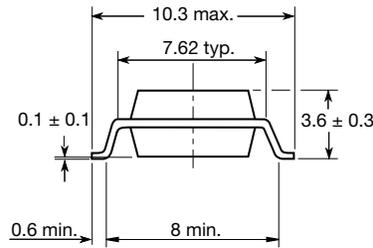
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Option 6

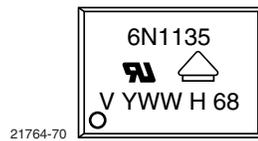


20802-12

Option 9



PACKAGE MARKING





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Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.